WEST Search History

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DATE: Thursday, May 18, 2006

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⊏	L13	L12 and substrate	212
⊏	L12	L11 and silicon layer	213
⊏	L11	L9 and polishing	388
⊏	L10	L9 and HF dip	23
⊏	L9	L8 and oxide layer	1140
⊏	L8	L7 and wafer	2548
⊏	L7	L6 and (die or dice)	5554
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⊏	L2	(SOI or silicon on insulator) same interconnect line	81
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END OF SEARCH HISTORY

For 10/784566